

C106 Series

Preferred Devices

Sensitive Gate Silicon Controlled Rectifiers

Reverse Blocking Thyristors

Glassivated PNP devices designed for high volume consumer applications such as temperature, light, and speed control; process and remote control, and warning systems where reliability of operation is important.

- Glassivated Surface for Reliability and Uniformity
- Power Rated at Economical Prices
- Practical Level Triggering and Holding Characteristics
- Flat, Rugged, Thermopad Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Sensitive Gate Triggering
- Device Marking: Device Type, e.g., C106B, Date Code

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) (Sine Wave, 50–60 Hz, $R_{GK} = 1\text{ k}\Omega$, $T_C = -40^\circ$ to 110°C)	V_{DRM} , V_{RRM}		Volts
C106B		200	
C106D, C106D1		400	
C106M, C106M1		600	
On-State RMS Current (180° Conduction Angles, $T_C = 80^\circ\text{C}$)	$I_{T(RMS)}$	4.0	Amps
Average On-State Current (180° Conduction Angles, $T_C = 80^\circ\text{C}$)	$I_{T(AV)}$	2.55	Amps
Peak Non-Repetitive Surge Current (1/2 Cycle, Sine Wave, 60 Hz, $T_J = +110^\circ\text{C}$)	I_{TSM}	20	Amps
Circuit Fusing Considerations ($t = 8.3\text{ ms}$)	I^2t	1.65	A^2s
Forward Peak Gate Power (Pulse Width $\leq 1.0\ \mu\text{sec}$, $T_C = 80^\circ\text{C}$)	P_{GM}	0.5	Watt
Forward Average Gate Power (Pulse Width $\leq 1.0\ \mu\text{sec}$, $T_C = 80^\circ\text{C}$)	$P_{G(AV)}$	0.1	Watt
Forward Peak Gate Current (Pulse Width $\leq 1.0\ \mu\text{sec}$, $T_C = 80^\circ\text{C}$)	I_{GM}	0.2	Amp
Operating Junction Temperature Range	T_J	-40 to +110	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-40 to +150	$^\circ\text{C}$
Mounting Torque (Note 2)	–	6.0	in. lb.

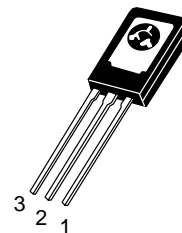
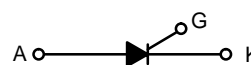
1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.
2. Torque rating applies with use of compression washer (B52200F006). Mounting torque in excess of 6 in. lb. does not appreciably lower case-to-sink thermal resistance. Anode lead and heatsink contact pad are common.



ON Semiconductor®

<http://onsemi.com>

SCRs
4 AMPERES RMS
200 thru 600 VOLTS



TO-225AA
(formerly TO-126)
CASE 077
STYLE 2

PIN ASSIGNMENT	
1	Cathode
2	Anode
3	Gate

ORDERING INFORMATION

Device	Package	Shipping
C106B	TO225AA	500/Box
C106D	TO225AA	500/Box
C106D1	TO225AA	500/Box
C106M	TO225AA	500/Box
C106M1	TO225AA	500/Box

Preferred devices are recommended choices for future use and best overall value.

C106 Series

Thermal Characteristics (T_C = 25°C unless otherwise noted.)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R _{θJC}	3.0	°C/W
Thermal Resistance, Junction to Ambient	R _{θJA}	75	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	T _L	260	°C

Electrical Characteristics (T_C = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Peak Repetitive Forward or Reverse Blocking Current (V _{AK} = Rated V _{DRM} or V _{RRM} , R _{GK} = 1000 Ohms)	I _{DRM} , I _{RRM}	T _J = 25°C	–	–	10	μA
T _J = 110°C		–	–	100	μA	

ON CHARACTERISTICS

Peak Forward On–State Voltage (Note 3) (I _{TM} = 4 A)	V _{TM}	–	–	2.2	Volts	
Gate Trigger Current (Continuous dc) (Note 4) (V _{AK} = 6 Vdc, R _L = 100 Ohms)	I _{GT}	T _J = 25°C	–	15	200	μA
T _J = –40°C		–	35	500		
Peak Reverse Gate Voltage (I _{GR} = 10 μA)	V _{GRM}	–	–	6.0	Volts	
Gate Trigger Voltage (Continuous dc) (Note 4) (V _{AK} = 6 Vdc, R _L = 100 Ohms)	V _{GT}	T _J = 25°C	0.4	0.60	0.8	Volts
T _J = –40°C		0.5	0.75	1.0		
Gate Non–Trigger Voltage (Continuous dc) (Note 4) (V _{AK} = 12 V, R _L = 100 Ohms, T _J = 110°C)	V _{GD}	0.2	–	–	Volts	
Latching Current (V _{AK} = 12 V, I _G = 20 mA)	I _L	T _J = 25°C	–	0.20	5.0	mA
T _J = –40°C		–	0.35	7.0		
Holding Current (V _D = 12 Vdc) (Initiating Current = 20 mA, Gate Open)	I _H	T _J = 25°C	–	0.19	3.0	mA
T _J = –40°C		–	0.33	6.0		
T _J = +110°C		–	0.07	2.0		

DYNAMIC CHARACTERISTICS

Critical Rate–of–Rise of Off–State Voltage (V _{AK} = Rated V _{DRM} , Exponential Waveform, R _{GK} = 1000 Ohms, T _J = 110°C)	dv/dt	–	8.0	–	V/μs
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3. Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2%.
4. R_{GK} is not included in measurement.

C106 Series

Voltage Current Characteristic of SCR

Symbol	Parameter
V_{DRM}	Peak Repetitive Off State Forward Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Off State Reverse Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Peak On State Voltage
I_H	Holding Current

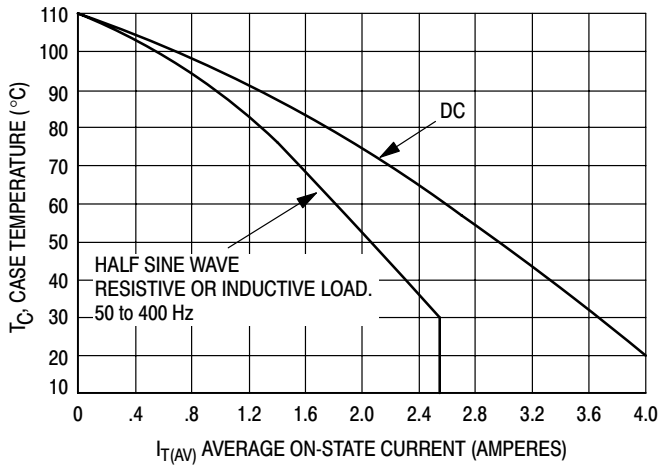
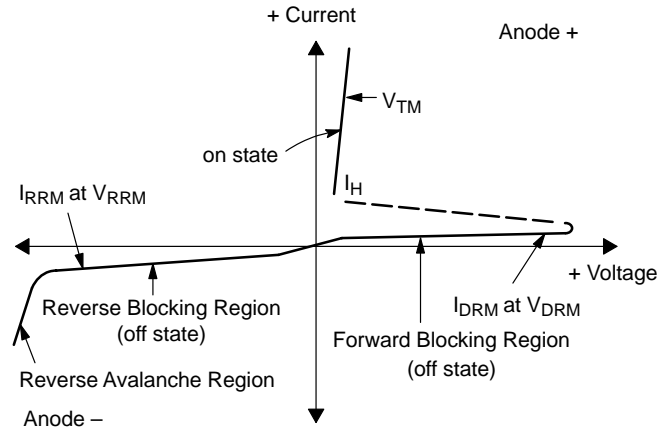


Figure 1. Average Current Derating

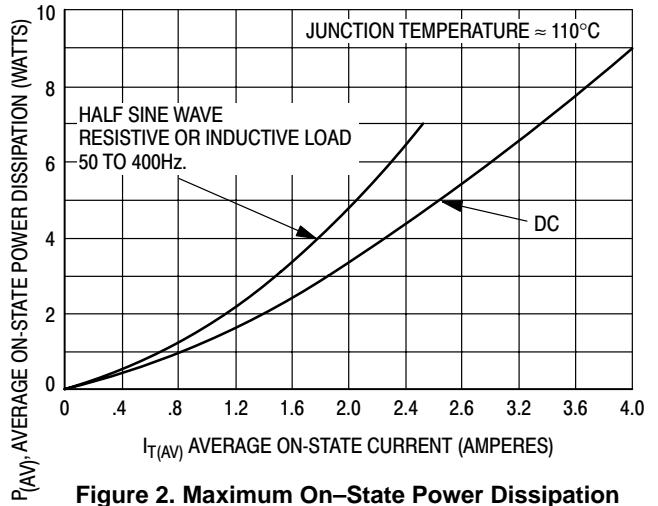


Figure 2. Maximum On-State Power Dissipation

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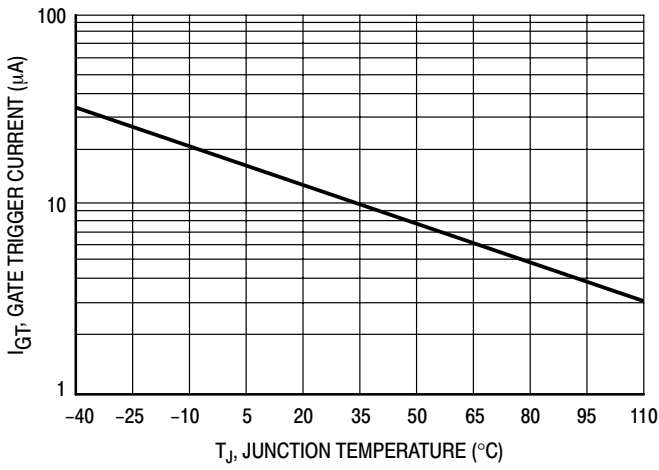


Figure 3. Typical Gate Trigger Current versus Junction Temperature

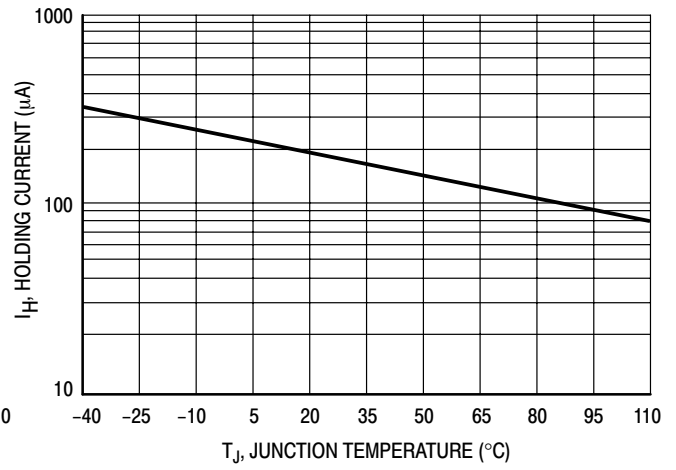


Figure 4. Typical Holding Current versus Junction Temperature

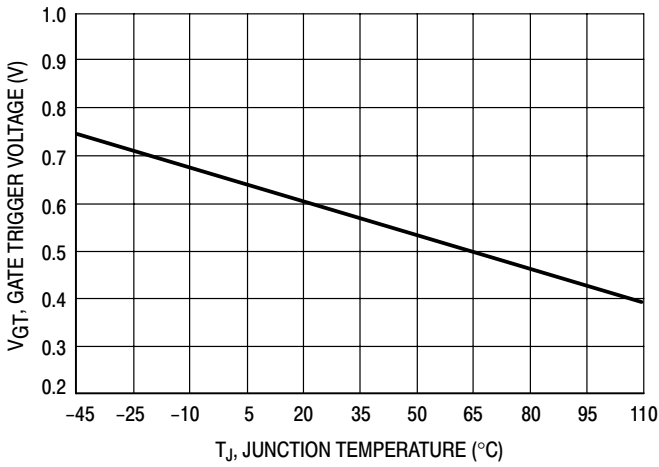


Figure 5. Typical Gate Trigger Voltage versus Junction Temperature

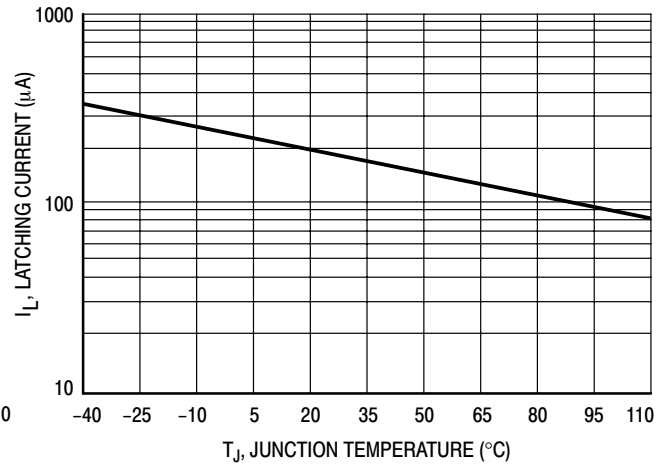
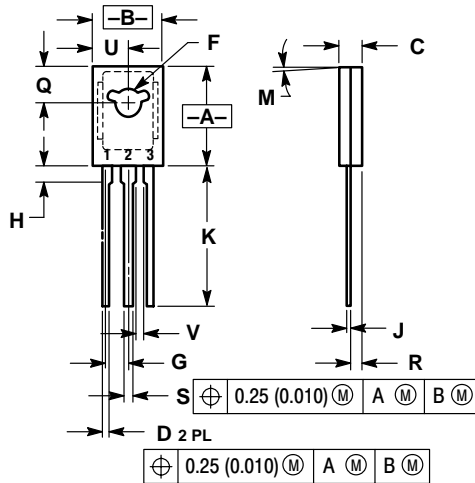


Figure 6. Typical Latching Current versus Junction Temperature

C106 Series

PACKAGE DIMENSIONS

TO-225AA
(formerly TO-126)
CASE 077-09
ISSUE W




- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.425	0.435	10.80	11.04
B	0.295	0.305	7.50	7.74
C	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094 BSC		2.39 BSC	
H	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
K	0.575	0.655	14.61	16.63
M	5° TYP		5° TYP	
Q	0.148	0.158	3.76	4.01
R	0.045	0.065	1.15	1.65
S	0.025	0.035	0.64	0.88
U	0.145	0.155	3.69	3.93
V	0.040	---	1.02	---

- STYLE 2:
PIN 1. CATHODE
2. ANODE
3. GATE

Notes

C106 Series

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